

Design of Si/poly-Si microrings

with complex waveguide cross-sections and minimal non-linearity

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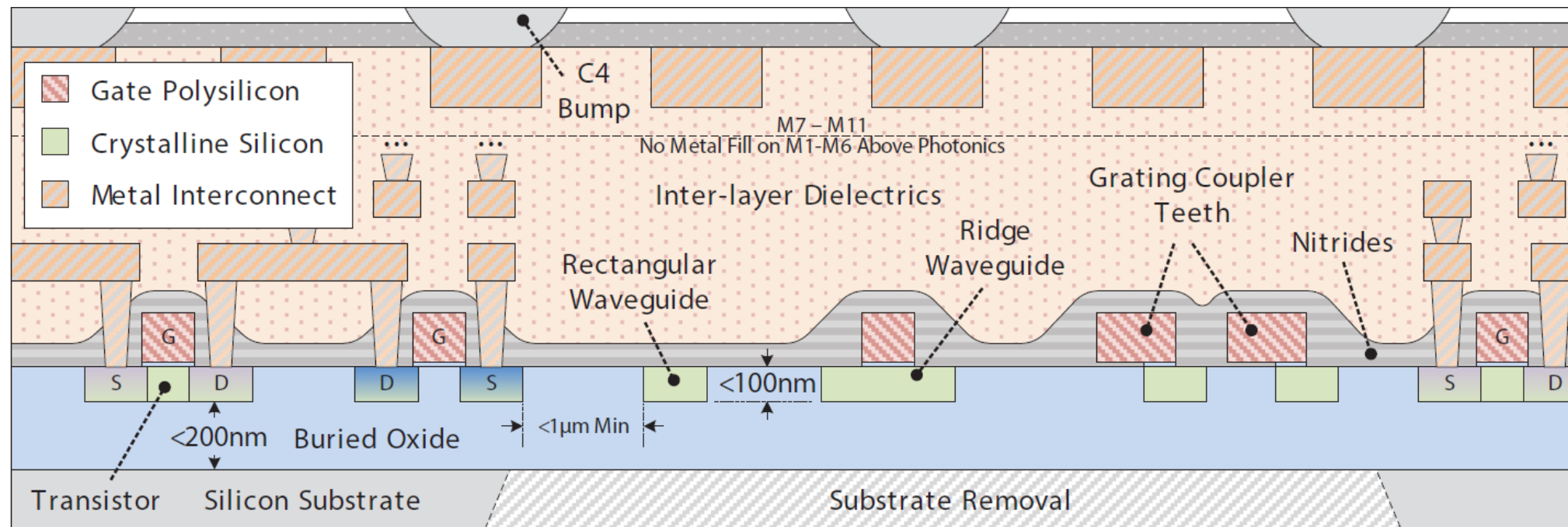
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Silicon Photonics

Cross-sectional view

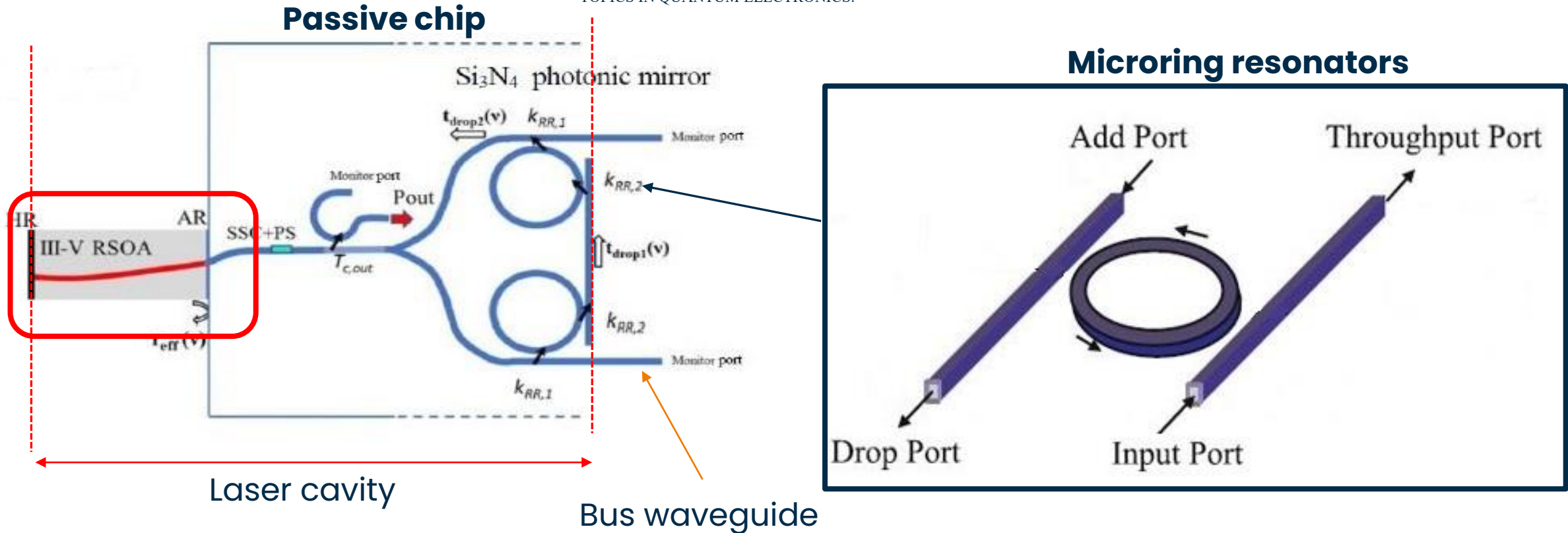
V.Stojanovic et al., Opt. Express, 26 (13106–13121), 2018



- A technology that allows creating photonic devices that use silicon as an optical medium, with the final goal of **integrating photonic and electronic devices on the same silicon chip**
- Main problem: efficient **laser sources**, monolithically integrated on Si, **are still missing**

Tunable Hybrid laser

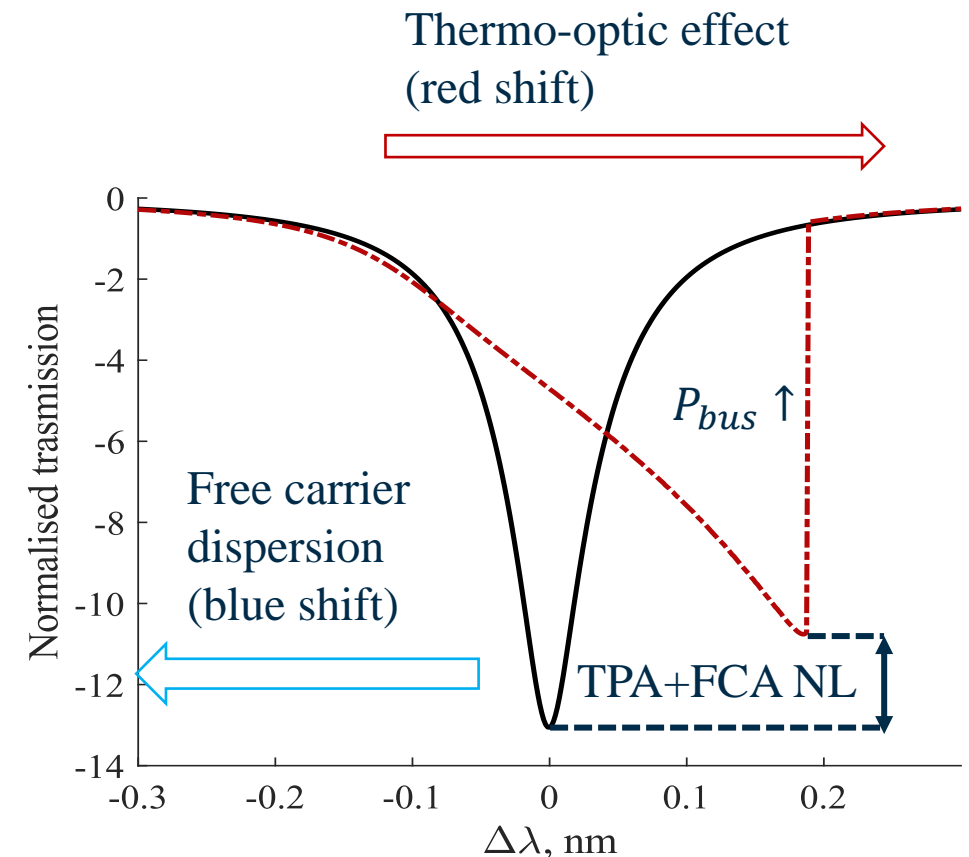
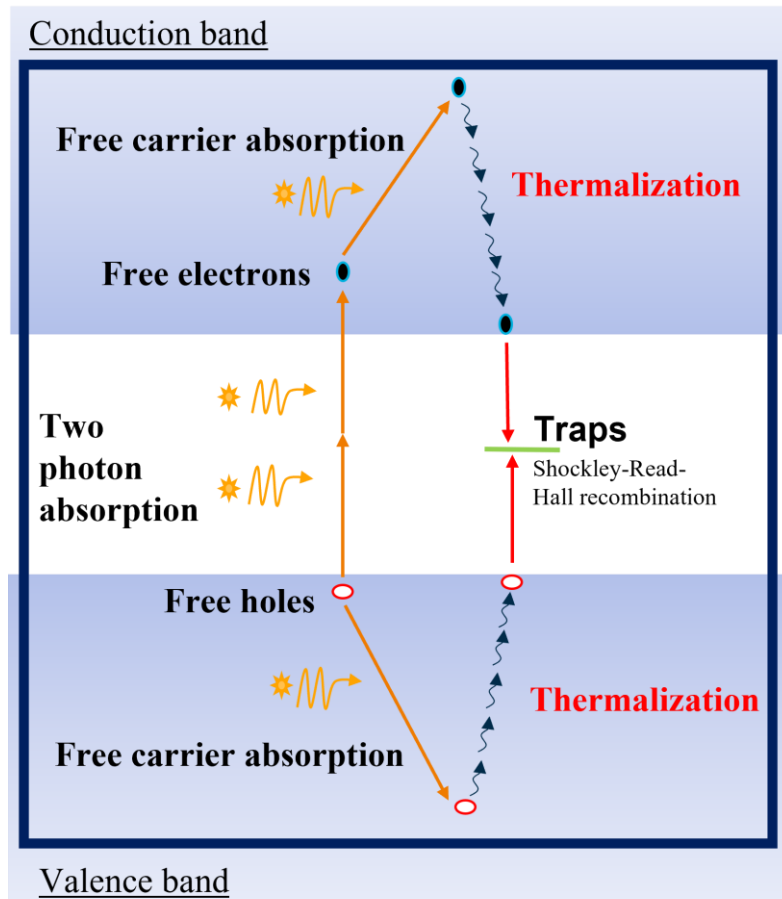
Lorenzo Columbo et al., "Efficient and Optical Feedback Tolerant Hybrid Laser Design for Silicon Photonics Applications" IEEE JOURNAL OF SELECTED TOPICS IN QUANTUM ELECTRONICS.



The **design of the passive chip** is crucial for improving the performances of these devices

Nonlinear effects in silicon

- The **SRH recombination** regulates the amount of free carriers, generated by **TPA**, that contribute to **nonlinear loss** and **free carrier dispersion**.



Models

Drift-diffusion equations

$$\begin{aligned}\nabla(-D_n \cdot \nabla n(x, y) + \mu_n \cdot n(x, y) \cdot \nabla \phi(x, y)) &= G_{ph}(x, y) - R_n(x, y) \\ \nabla(-D_p \cdot \nabla p(x, y) - \mu_p \cdot p(x, y) \cdot \nabla \phi(x, y)) &= G_{ph}(x, y) - R_p(x, y) \\ \nabla^2 \phi(x, y) &= \frac{q}{\epsilon} (p(x, y) - n(x, y) + N_a^- - f_t N_t)\end{aligned}$$

$$G_{ph}(x, y) = \frac{P_c^2}{hc} \beta_{TPA} \frac{n^2}{Z_0^2 8 P_\mu^2} |E_\mu(x, y)|^4$$

Shockley-Read-Hall recombination

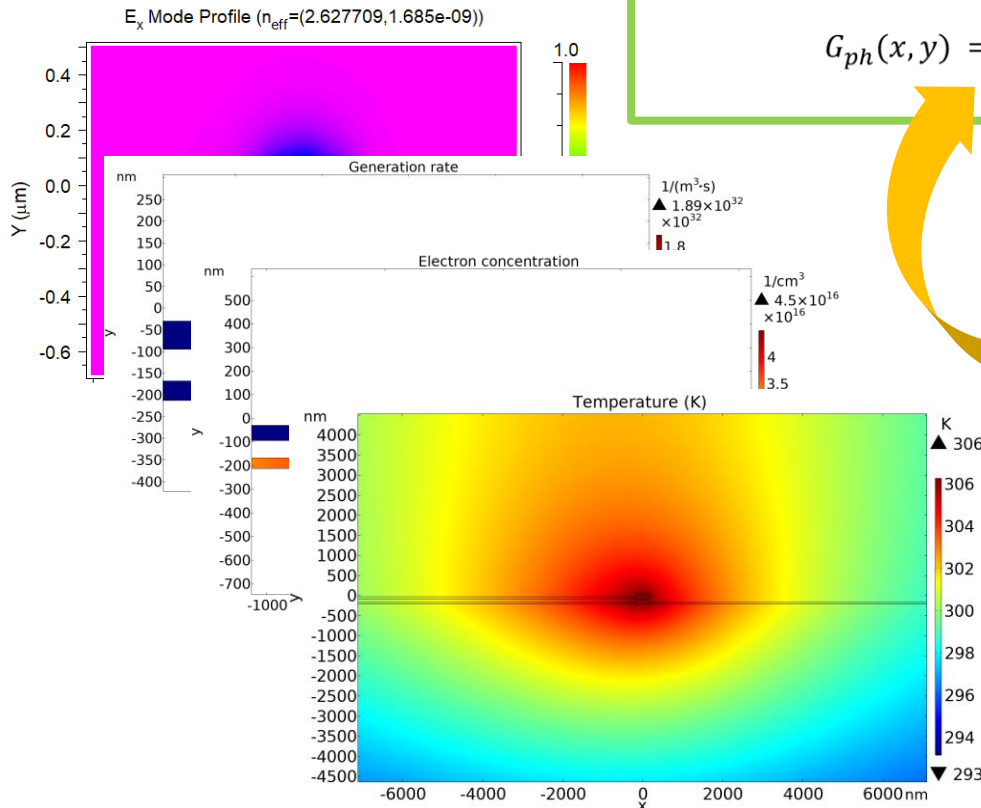
$$R_n(x, y) = C_n \cdot N_t \cdot n(x, y) (1 - f_t) \left(1 - e^{\frac{E_{ft} - E_{fn}}{k_b T}}\right)$$

$$R_p(x, y) = C_p \cdot N_t \cdot p(x, y) f_t \left(1 - e^{\frac{E_{fp} - E_{ft}}{k_b T}}\right)$$

$$f_t = \frac{1}{1 + g_D \cdot e^{\frac{E_t - E_{ft}}{k_b T}}}$$

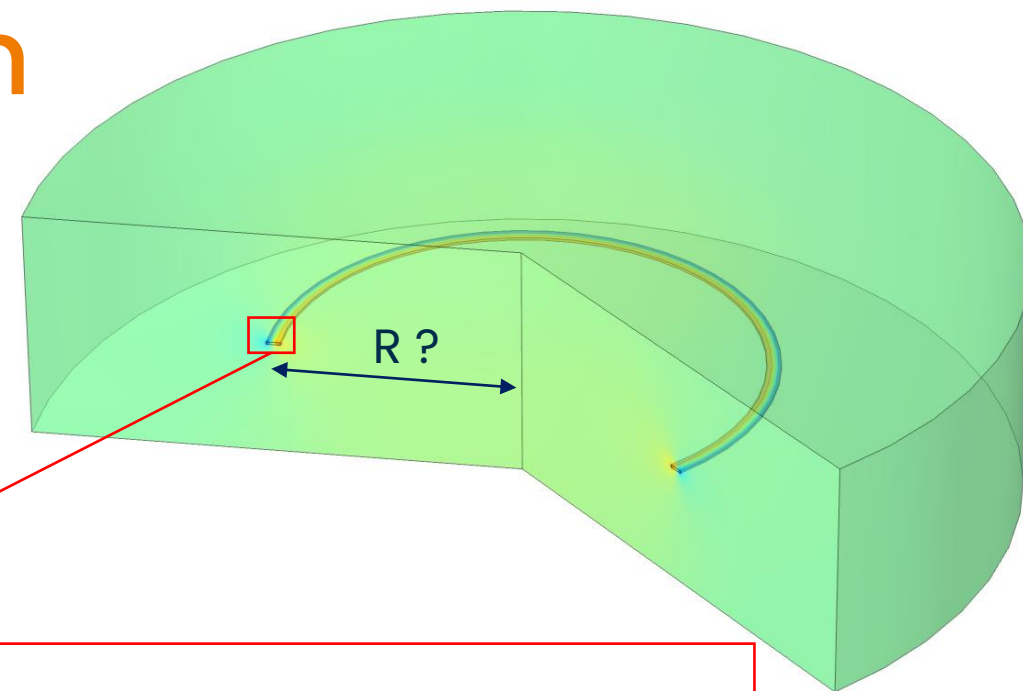
$$\begin{aligned}d_z \cdot \rho \cdot C_p \cdot u \cdot \nabla T - \nabla(d_z \cdot k \nabla T) &= d_z Q(x, y) \\ Q(x, y) &= \frac{|J_n|^2}{\sigma_n} + \frac{|J_p|^2}{\sigma_p} + \Delta \alpha_{FCD} \cdot I_{opt} + R_{n,p} \cdot 2 \hbar \omega\end{aligned}$$

Thermal model

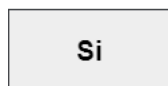


Design in SISCAP platform

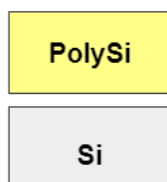
Silicon Insulator Silicon Capacitor



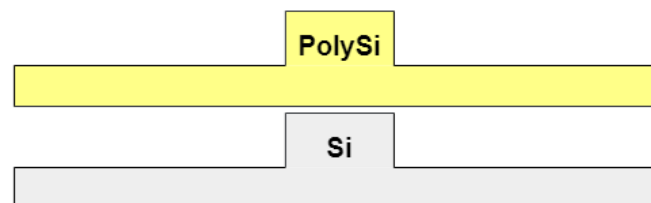
Si Strip



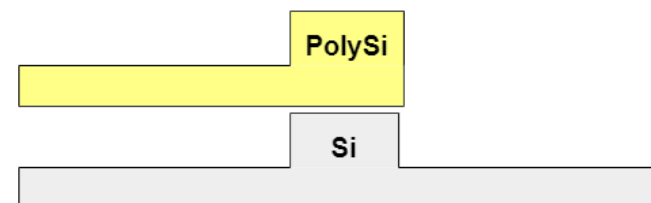
Si/PolySi Strip



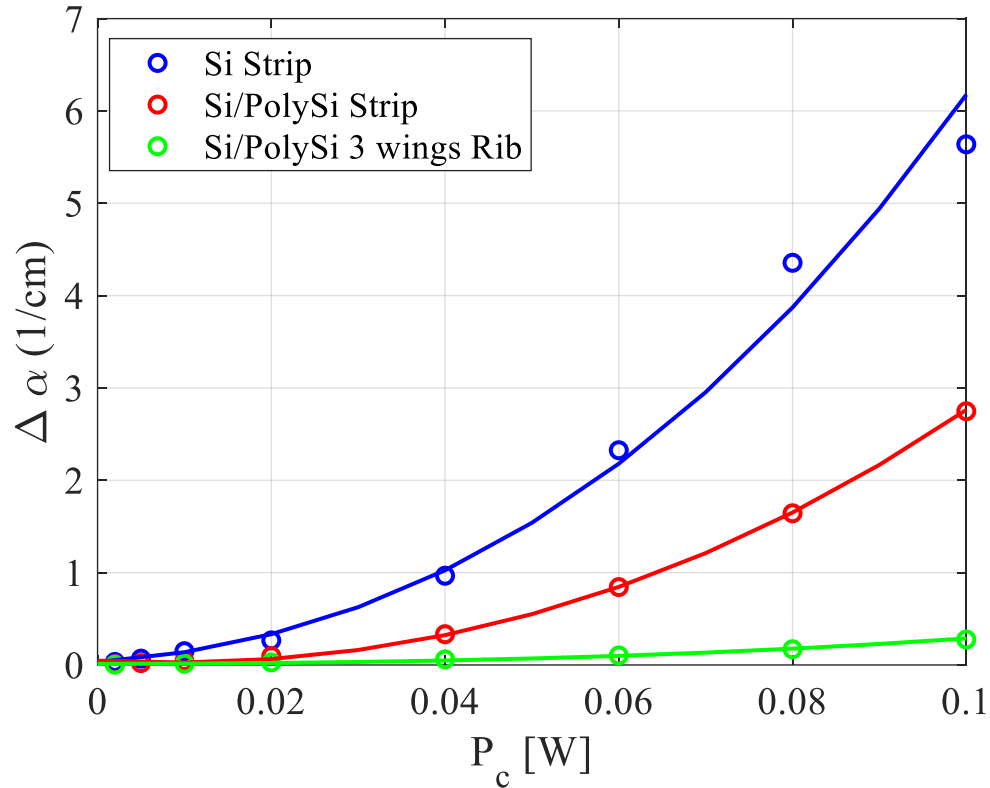
Si/PolySi 4 wings Rib



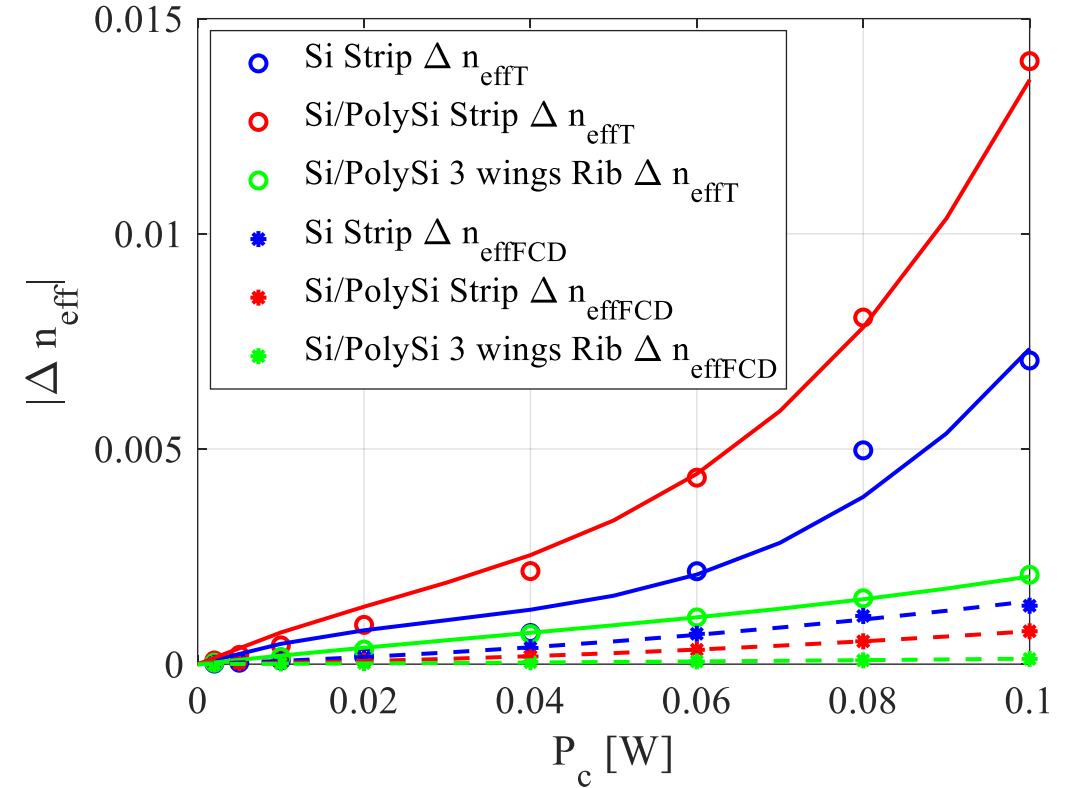
Si/PolySi 3 wings Rib



Data processing

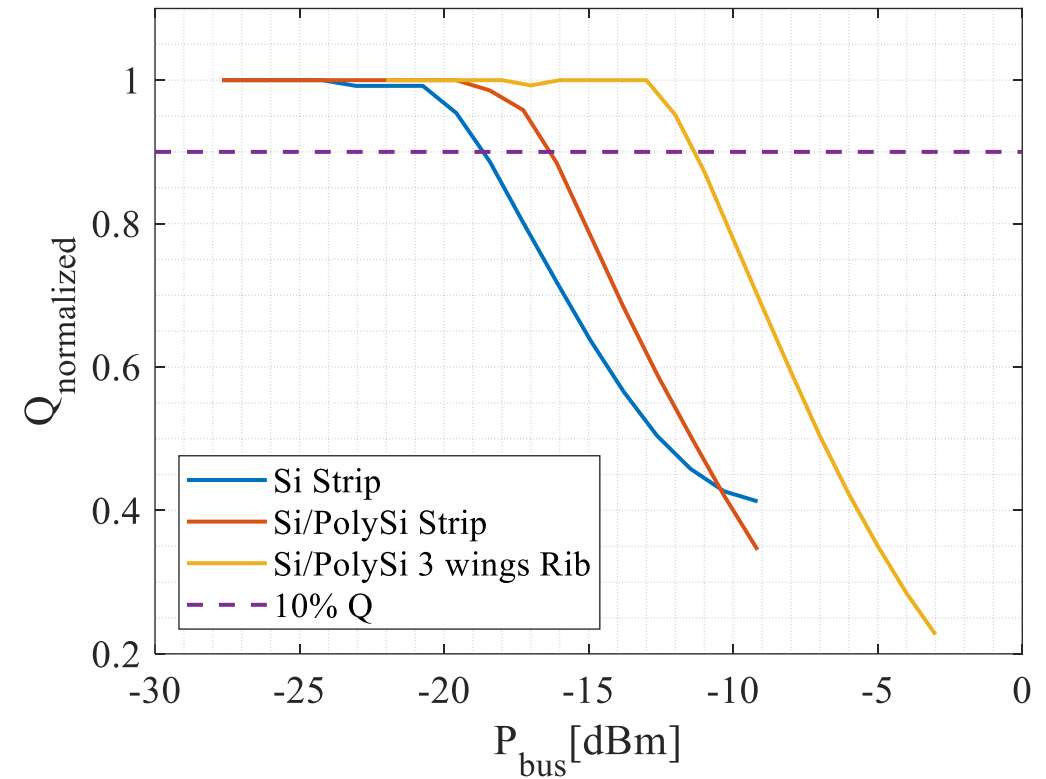
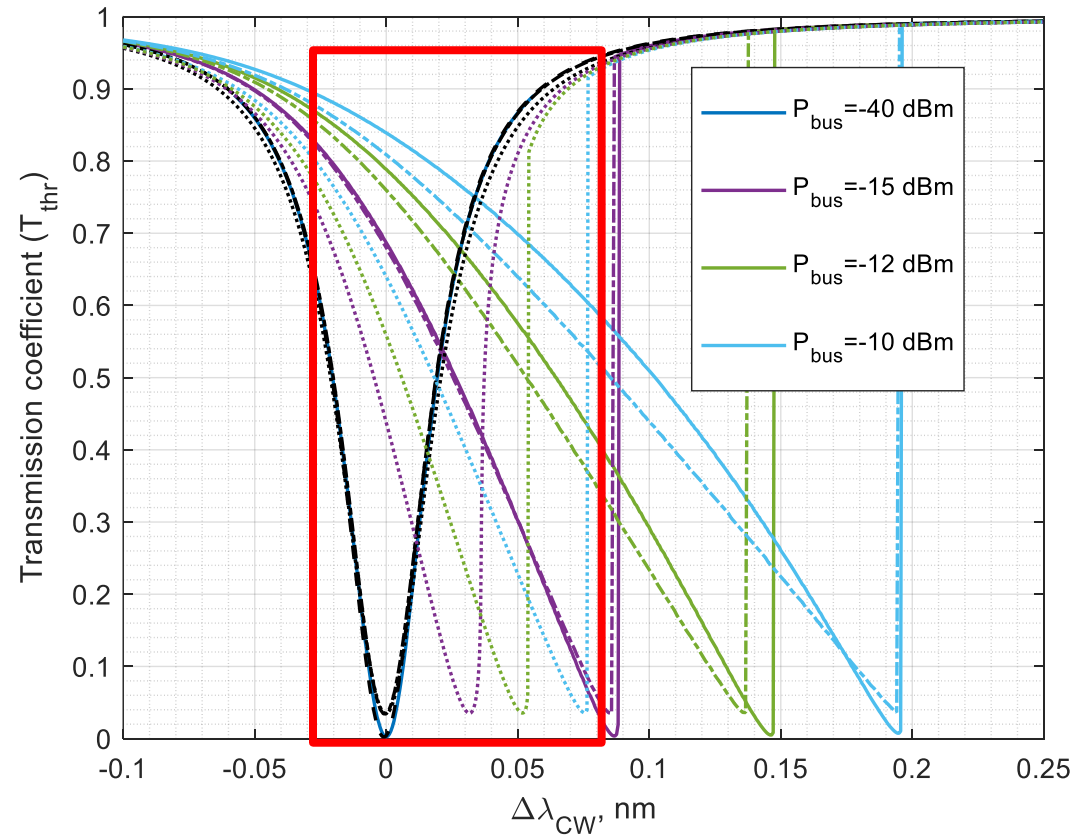


$$\Delta\alpha = \frac{2c \cdot \epsilon_0 \cdot n \int \int_{\infty} \frac{\Delta\alpha_{FC}(x,y)\lambda}{4\pi} \cdot |E(x,y)|^2 dx dy}{\int \int_{\infty} \text{Re}\{E(x,y) \times H(x,y)^*\} \cdot e_z dx dy}$$



$$\Delta n_{effFCD,T} = \frac{c \cdot \epsilon_0 \cdot n \int \int_{\infty} \Delta n_{FCD,T}(x,y) \cdot |E(x,y)|^2 dx dy}{\int \int_{\infty} \text{Re}\{E(x,y) \times H(x,y)^*\} \cdot e_z dx dy}$$

Final Results



Transmission spectra of the 3 MRRs at different bus input power:

- Si strip (continuous)
- Si/PolySi strip (dash-dotted)
- **Si/PolySi 3 wings Rib guide** (dotted)